Amendments to the Claims

This listing of claims replaces all prior versions:

1. (Currently Amended) A method for forming a silicide conductive structure on a semiconductor device, the method comprising;

depositing metal on the surface of a patterned semiconductor film;

heat treating the semiconductor film on which the metal is deposited;

removing residual metal that did not react during the heat treatment step; [[and]]

repeating a sequence of the depositing step, the heat treating step, and the removing step once or a number of times; and

forming a C54 phase titanium silicide film by performing the repeating step.

2. (Original) The method for manufacturing the semiconductor device according to claim 1, further comprising:

heat treating the semiconductor film after the repeating step at a temperature that is higher than that of the heat treating step.

3. (Original) The method for manufacturing the semiconductor device according to claim 2, wherein the patterned semiconductor film is an N-type semiconductor.

4. (Currently Amended) A method for manufacturing a semiconductor device, comprising:

forming a conductive portion on the substrate, wherein the conductive portion includes a gate electrode;

forming a spacer on a side wall of the gate electrode;

depositing meal on the surface of the substrate including the conductive portion;

applying silicide on the conductive portion in a self-aligned manner by heat treating the substrate on which the metal is deposited;

removing residual metal that did not react during the heat treatment; [[and]]

repeating a sequence of the depositing step, the silicide applying step, and the removing step once or a number of times; and

forming a C54 phase titanium silicide film by performing the repeating step.

5. (Original) The method for manufacturing the semiconductor device according to claim 4, further comprising:

heat treating the substrate after the repeating step at a temperature that is higher than that of the heating treating step.

6. (Original) The method for manufacturing the semiconductor device according to claim 5, wherein the conductive portion to which silicide is applied is an N-type semiconductor.

7. (Original) The method for manufacturing the semiconductor device according to claim 4, wherein the thickness of the gate electrode is 1,000Å (10^{-8}cm) to 2,500Å (10^{-8}cm), and the heat treating is repeated in a temperature range of 600°C to 720°C.

8. (Original) The method for manufacturing the semiconductor device according to claim 7, further comprising:

heat treating the substrate after the repeating step for 30 seconds at a temperature of about 850°C.

9. (Original) The method for manufacturing the semiconductor device according to claim 8, wherein the conductive portion to which silicide is applied is an N-type semiconductor.